

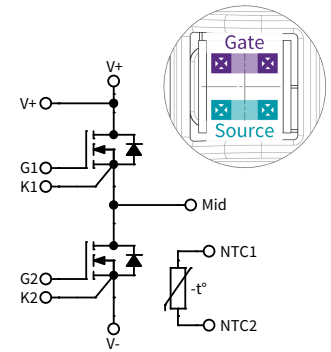
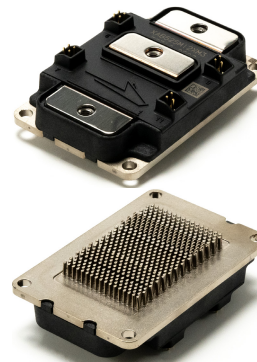
# CAB525F12XM3

1200 V, 2.6 mΩ, Silicon Carbide, Half-Bridge Module

$V_{DS}$	1200 V
$I_{DS}$	525 A <sub>RMS</sub>

## Technical Features

- High Power Density Footprint
- High Junction Temperature (175 °C) Operation
- Low-Inductance (6.7 nH) Design
- Implements WolfSpeed's Third Generation SiC MOSFET Technology
- Silicon Nitride Insulator and Copper Baseplate
- Advanced Direct Cooling Baseplate



## Typical Applications

- Motor and Motion Control
- Vehicle Fast Chargers
- Uninterruptable Power Supplies
- Smart-Grid / Grid-Tied Distributed Generation
- Traction Drives
- E-mobility

## System Benefits

- Terminal layout allows for direct bus bar connection without bends or bushings enabling a simple, low-inductance design.
- Isolated, integrated temperature sensing enables high-level temperature protection.
- Dedicated high-side Kelvin-drain pin enables direct voltage sensing for gate driver overcurrent protection.

## Key Parameters

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions	Notes
Drain-Source Voltage	$V_{DS}$			1200	V	$T_F = 25\text{ °C}$	Note 1 Fig. 34
Maximum Gate-Source Voltage	$V_{GS\text{ max}}$	-8		+19		Transient	
Operational Gate-Source Voltage	$V_{GS\text{ op}}$		-4/+15			Static	
Implementable Current, Inverter Operation	$I_{IMP}$			525	A <sub>RMS</sub>	$T_F = 60\text{ °C}$ , $F_S = 5\text{ kHz}$	Fig. 22
DC Continuous Drain Current, Flow Rate = 4 LPM	$I_D$			450	A	$V_{GS} = 15\text{ V}$ , $T_F = 25\text{ °C}$ , $T_{VJ} \leq 175\text{ °C}$	Notes 2, 3, 4 Fig. 20
			411			$V_{GS} = 15\text{ V}$ , $T_F = 60\text{ °C}$ , $T_{VJ} \leq 175\text{ °C}$	
Pulsed Drain Current	$I_{DM}$		1050			$t_{Pmax}$ limited by $T_{VJ\text{ op}}$ $V_{GS} = 15\text{ V}$ , $T_F = 25\text{ °C}$	
Power Dissipation	$P_D$		1034		W	$T_F = 25\text{ °C}$ , $T_{VJ} \leq 175\text{ °C}$	Note 5 Fig. 21
Operational Virtual Junction Temperature	$T_{VJ(op)}$	-40		175	°C		

Note (1): Recommended turn-on gate voltage is 15V with ±5% regulation tolerance

Note (2): Current limit at  $T_F = 25\text{ °C}$  imposed by package

Note (3): Current limit  $T_F = 60\text{ °C}$  calculated by  $I_{D(max)} = \sqrt{(P_D / R_{DS(typ)}(T_{J(max)}, I_{D(max)}))}$

Note (4): Verified by design

Note (5):  $P_D = (T_{VJ} - T_F) / R_{TH(JF, Typ)}$


**MOSFET Characteristics (Per Position) ( $T_{vj} = 25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions	Notes
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200				$V_{GS} = 0\text{ V}$ , $T_{vj} = -40^\circ\text{C}$	
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.5	3.6	V	$V_{DS} = V_{GS}$ , $I_{DS} = 140\text{ mA}$	
			2.0			$V_{DS} = V_{GS}$ , $I_{DS} = 140\text{ mA}$ , $T_{vj} = 175^\circ\text{C}$	
Zero Gate Voltage Drain Current	$I_{DSS}$		5	200	$\mu\text{A}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 1200\text{ V}$	
Gate-Source Leakage Current	$I_{GSS}$		50	1300	nA	$V_{GS} = 15\text{ V}$ , $V_{DS} = 0\text{ V}$	
Drain-Source On-State Resistance (MOSFET Only)	$R_{DS(on)}$		2.6	3.4	m $\Omega$	$V_{GS} = 15\text{ V}$ , $I_D = 450\text{ A}$	Fig. 2 Fig. 3
			4.7			$V_{GS} = 15\text{ V}$ , $I_D = 450\text{ A}$ , $T_{vj} = 175^\circ\text{C}$	
Transconductance	$g_{fs}$		348		S	$V_{DS} = 20\text{ V}$ , $I_D = 450\text{ A}$	Fig. 4
			333			$V_{DS} = 20\text{ V}$ , $I_D = 450\text{ A}$ , $T_{vj} = 175^\circ\text{C}$	
Turn-On Switching Energy, $T_{vj} = 25^\circ\text{C}$ , $T_{vj} = 125^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	$E_{On}$		25.4 24.0 24.4		mJ	$V_{DD} = 600\text{ V}$ , $I_D = 450\text{ A}$ , $V_{GS} = -4\text{ V}/15\text{ V}$ , $R_{G-ON(ext)} = 4.0\text{ }\Omega$ , $R_{G-OFF(ext)} = 0.0\text{ }\Omega$ , $L_G = 10.2\text{ nH}$	Fig. 11 Fig. 13
Turn-Off Switching Energy, $T_{vj} = 25^\circ\text{C}$ , $T_{vj} = 125^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	$E_{Off}$		7.5 8.1 8.4				
Internal Gate Resistance	$R_{G(int)}$		2.5		$\Omega$	$f = 100\text{ kHz}$	
Input Capacitance	$C_{iss}$		38		nF	$V_{GS} = 0\text{ V}$ , $V_{DS} = 800\text{ V}$ , $V_{AC} = 25\text{ mV}$ , $f = 100\text{ kHz}$	Fig. 9
Output Capacitance	$C_{oss}$		1.5				
Reverse Transfer Capacitance	$C_{rss}$		35		pF		
Gate to Source Charge	$Q_{GS}$		385		nC	$V_{DS} = 800\text{ V}$ , $V_{GS} = -4\text{ V}/15\text{ V}$ , $I_D = 450\text{ A}$ , Per IEC60747-8-4 pg 21	
Gate to Drain Charge	$Q_{GD}$		475				
Total Gate Charge	$Q_G$		1300				
FET Thermal Resistance, Junction to Fluid	$R_{th JF}$		0.145		$^\circ\text{C/W}$	4 LPM per Module; $T_F = 60^\circ\text{C}$	Fig. 17

**Diode Characteristics (Per Position) ( $T_{vj} = 25^\circ\text{C}$  unless otherwise specified)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions	Notes
Body Diode Forward Voltage	$V_{SD}$		4.7		V	$V_{GS} = -4\text{ V}$ , $I_{SD} = 450\text{ A}$	Fig. 7
			4.2			$V_{GS} = -4\text{ V}$ , $I_{SD} = 450\text{ A}$ , $T_{vj} = 175^\circ\text{C}$	
Reverse Recovery Time	$t_{RR}$		78		ns	$V_{GS} = -4\text{ V}$ , $I_{SD} = 450\text{ A}$ , $V_R = 600\text{ V}$ , $di/dt = 5.1\text{ A/ns}$ , $R_{G-ON(ext)} = 4.0\text{ }\Omega$ , $T_{vj} = 175^\circ\text{C}$	
Reverse Recovery Charge	$Q_{RR}$		7.2		$\mu\text{C}$		
Peak Reverse Recovery Current	$I_{RRM}$		169		A		
Reverse Recovery Energy, $T_{vj} = 25^\circ\text{C}$ , $T_{vj} = 125^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	$E_{RR}$		0.2 0.9 1.1		mJ	$V_{DD} = 600\text{ V}$ , $I_D = 450\text{ A}$ , $V_{GS} = -4\text{ V}/15\text{ V}$ , $R_{G-ON(ext)} = 4.0\text{ }\Omega$ , $L_G = 10.2\text{ nH}$	Fig. 14



Temperature Sensor (NTC) Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Resistance at 25 °C	R <sub>25</sub>		4700		Ω	T <sub>NTC</sub> = 25 °C
Tolerance of R <sub>25</sub>				±1	%	
Beta Value for 25°C to 85°C	B <sub>25/85</sub>		3435		K	
Beta Value for 0°C to 100°C	B <sub>0/100</sub>		3399		K	
Tolerance of B <sub>25/85</sub>				±1	%	
Maximum Power Dissipation	P <sub>25</sub>			50	mW	

Steinhart & Hart Coefficients for NTC Resistance & NTC Temperature Computation (T in K)

$$\ln\left(\frac{R}{R_{25}}\right) = A + \frac{B}{T} + \frac{C}{T^2} + \frac{D}{T^3}$$

A	B	C	D
-1.289E+01	4.245E+03	-8.749E+04	-9.588E+06

$$\frac{1}{T} = A_1 + B_1 \ln\left(\frac{R}{R_{25}}\right) + C_1 \ln^2\left(\frac{R}{R_{25}}\right) + D_1 \ln^3\left(\frac{R}{R_{25}}\right)$$

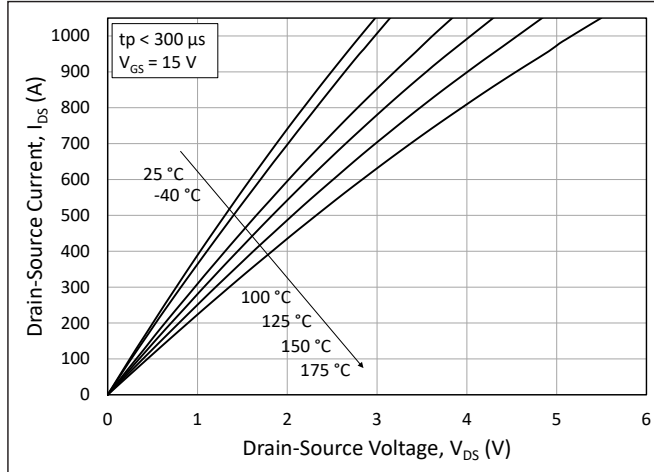
A <sub>1</sub>	B <sub>1</sub>	C <sub>1</sub>	D <sub>1</sub>
3.354E-03	3.001E-04	5.085E-06	2.188E-07

Module Physical Characteristics

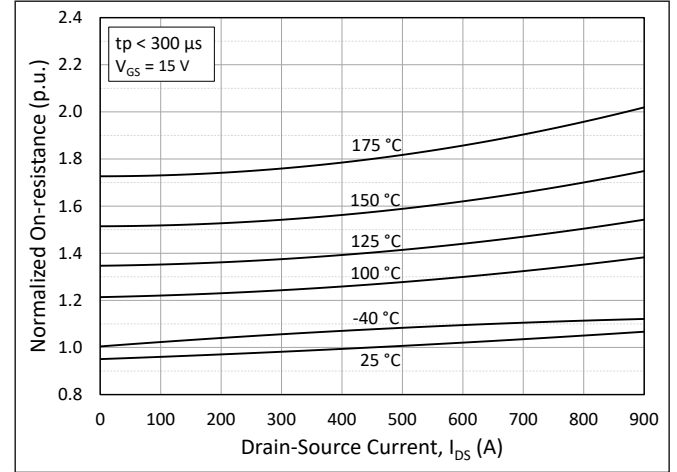
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Package Resistance, M1 (High-Side)	R <sub>3-1</sub>		0.72		mΩ	T <sub>c</sub> = 125°C, Note 6 & 7
Package Resistance, M2 (Low-Side)	R <sub>1-2</sub>		0.63			T <sub>c</sub> = 125°C, Note 6 & 7
Stray Inductance	L <sub>stray</sub>		6.7		nH	Between terminals 2 & 3, f = 10 MHz
Case Temperature	T <sub>c</sub>	-40		125	°C	
Mounting Torque	M <sub>s</sub>	2.0	3.0	4.0	N-m	Baseplate, M4 bolts
		2.0	4.0	5.0		Power Terminals, M5 bolts
Weight	W		188		g	
Case Isolation Voltage	V <sub>isol</sub>	4.0			kV	AC, 50 Hz, 1 minute
Comparative Tracking Index	CTI	600				
Clearance Distance		12.5			mm	From 2 to 3, Note 7
		11.5				From 1 to Baseplate, Note 7
		5.7				From 2 to 5, Note 7
		13.7				From 5 to Baseplate, Note 7
Creepage Distance		14.7				From 2 to 3, Note 7
		14.0				From 1 to Baseplate, Note 7
		14.7				From 2 to 5, Note 7
		14.3				From 5 to Baseplate, Note 7

Note (6): Total Effective Resistance (Per Switch Position) = MOSFET R<sub>DS(on)</sub> + Switch Position Package Resistance  
Note (7): Numbers reference the connections from the Schematics and Pin Out section of this document

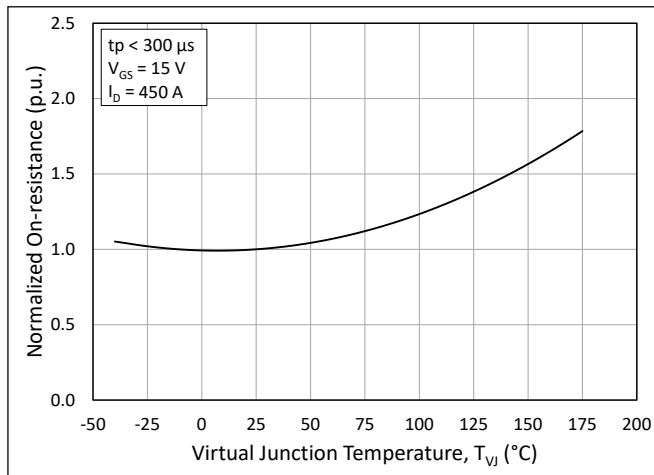
## Typical Performance



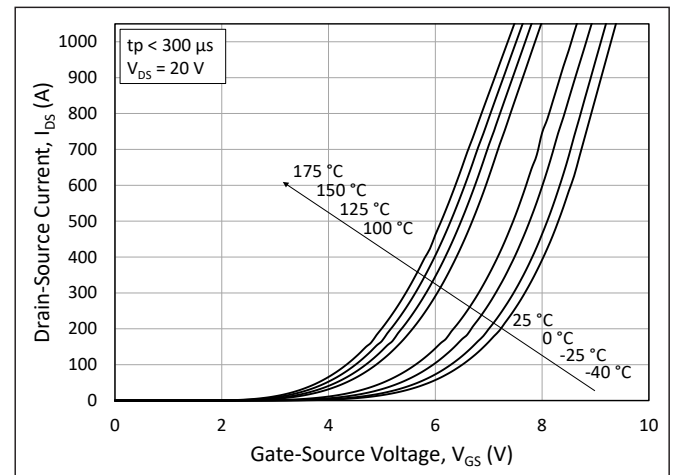
**Figure 1.** Output Characteristics for Various Junction Temperatures



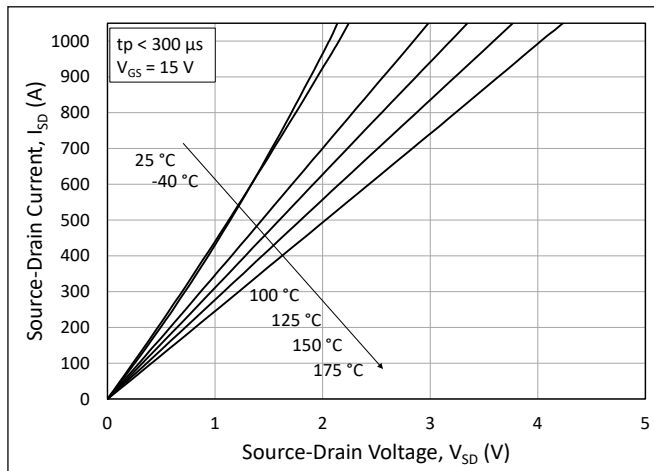
**Figure 2.** Normalized On-State Resistance vs. Drain Current for Various Junction Temperatures



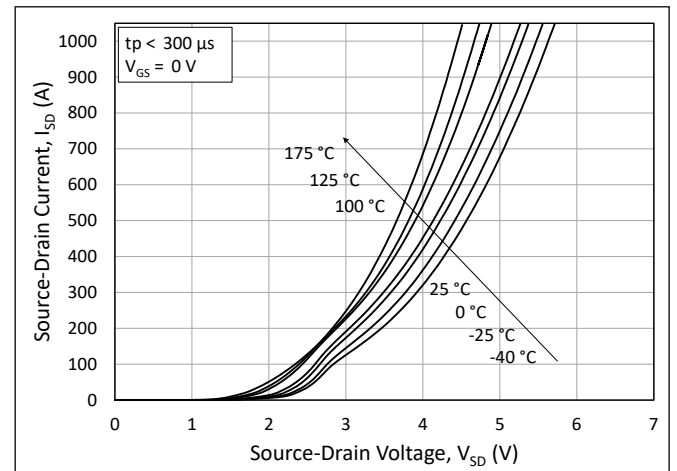
**Figure 3.** Normalized On-State Resistance vs. Junction Temperature



**Figure 4.** Transfer Characteristic for Various Junction Temperatures

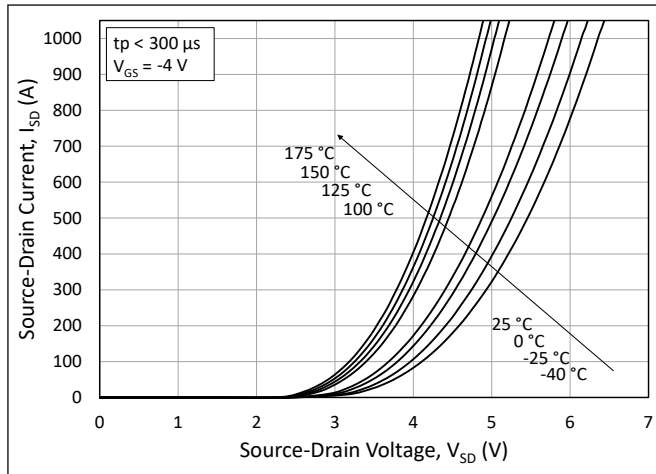


**Figure 5.** 3<sup>rd</sup> Quadrant Characteristic vs. Junction Temperatures at  $V_{GS} = 15$  V

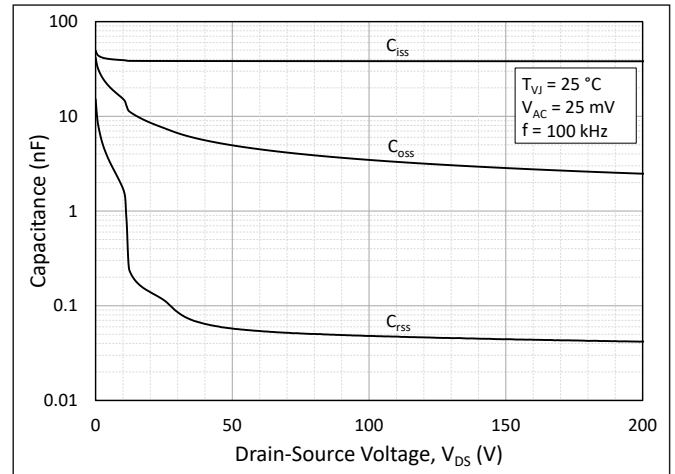


**Figure 6.** 3<sup>rd</sup> Quadrant Characteristic vs. Junction Temperatures at  $V_{GS} = 0$  V (Body Diode)

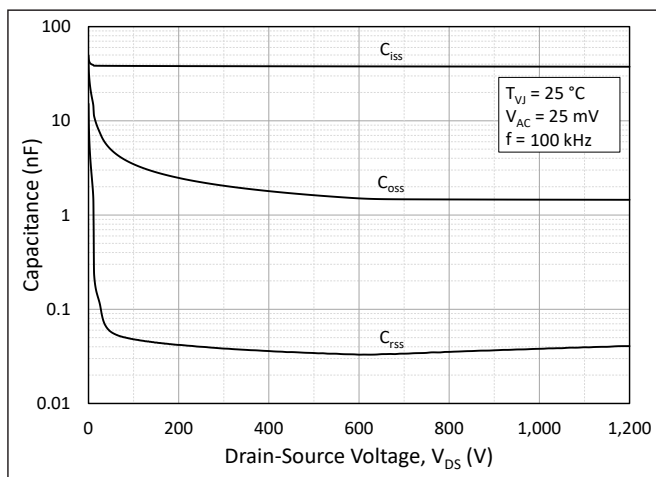
## Typical Performance



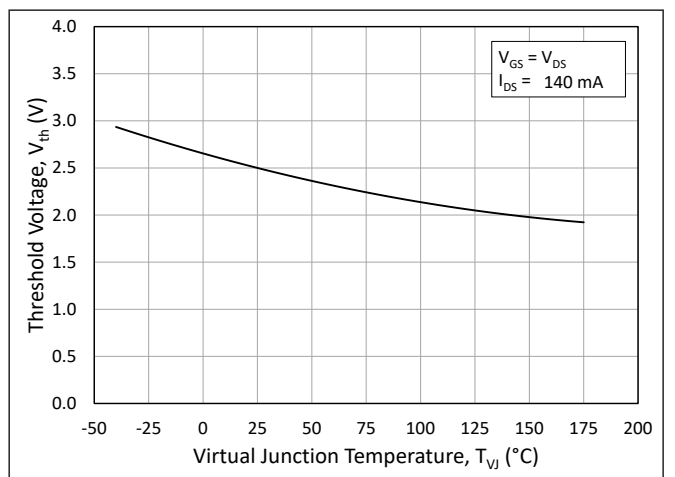
**Figure 7.** 3<sup>rd</sup> Quadrant Characteristic vs. Junction Temperatures at  $V_{GS} = -4$  V (Body Diode)



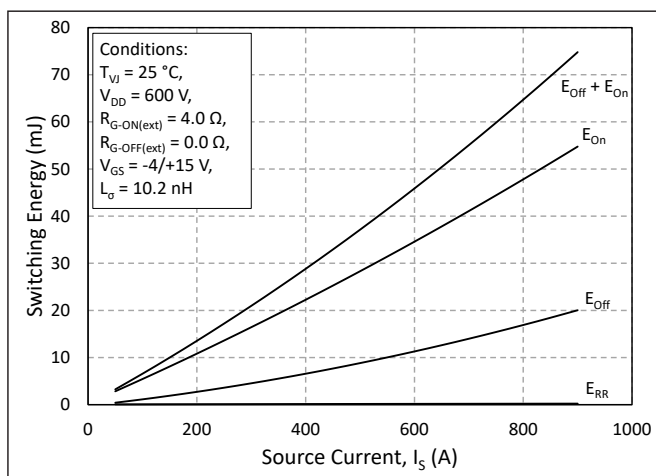
**Figure 8.** Typical Capacitances vs. Drain to Source Voltage (0 - 200V)



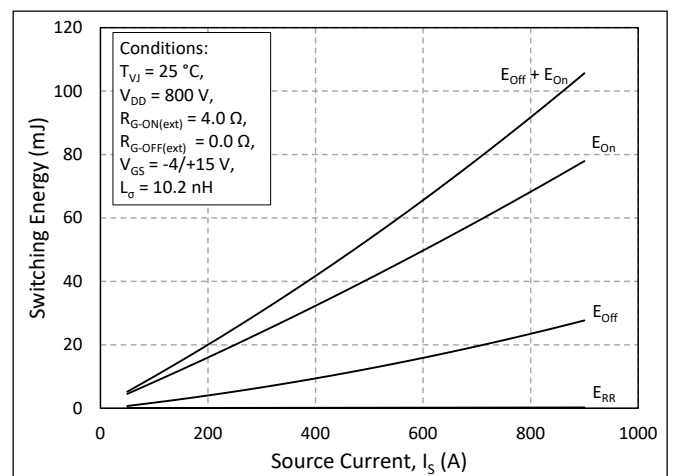
**Figure 9.** Typical Capacitances vs. Drain to Source Voltage (0 - 1200V)



**Figure 10.** Threshold Voltage vs. Junction Temperature

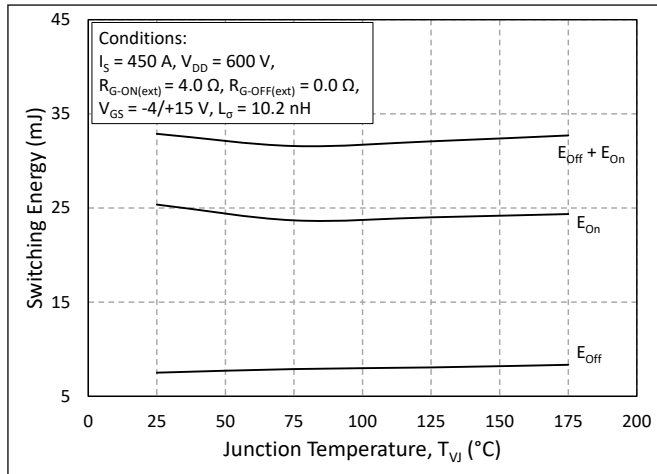


**Figure 11.** Switching Energy vs. Drain Current ( $V_{DD} = 600$  V)

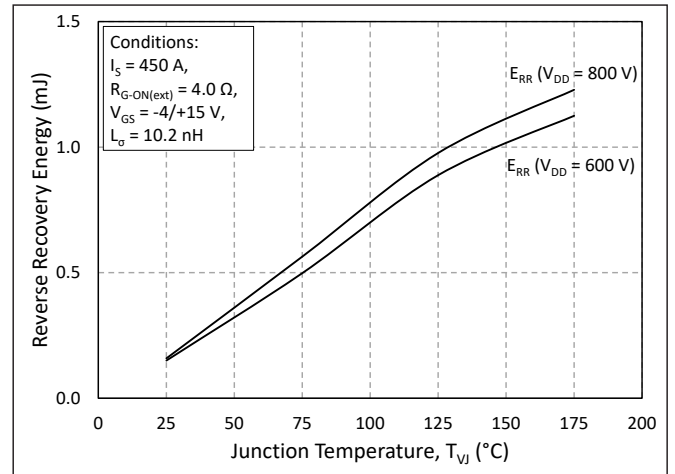


**Figure 12.** Switching Energy vs. Drain Current ( $V_{DD} = 800$  V)

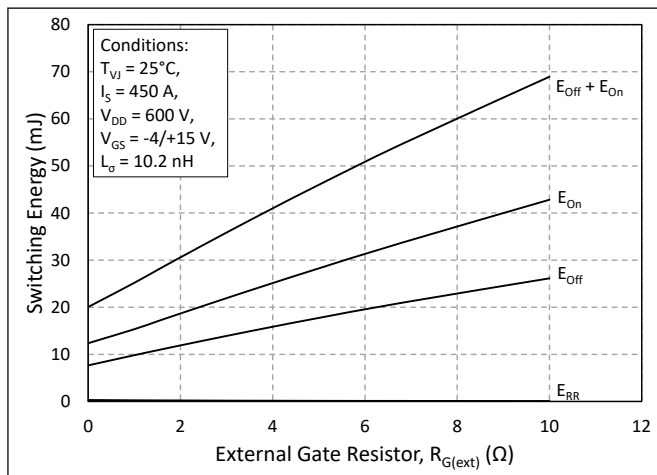
## Typical Performance



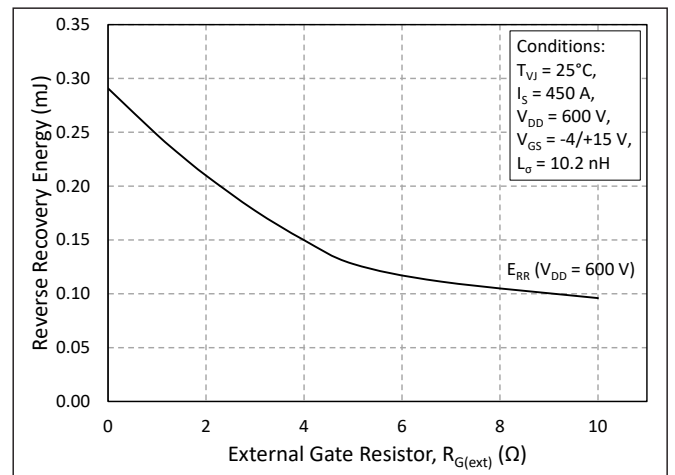
**Figure 13.** MOSFET Switching Energy vs. Junction Temperature



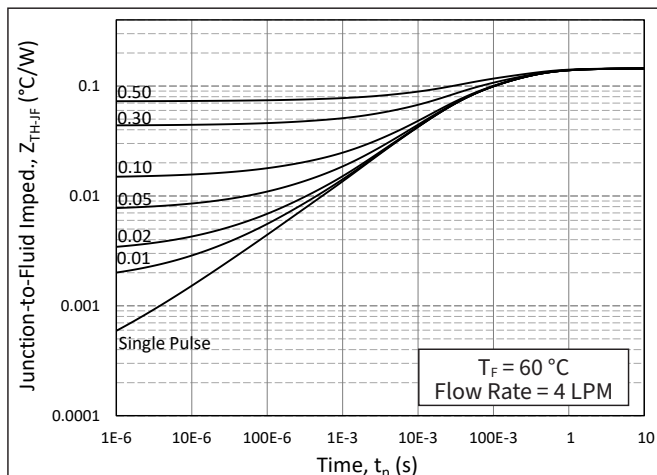
**Figure 14.** Reverse Recovery Energy vs. Junction Temperature



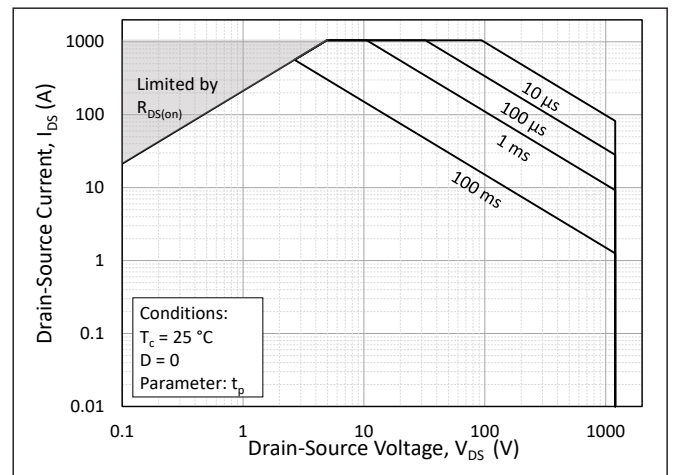
**Figure 15.** MOSFET Switching Energy vs. External Gate Resistance



**Figure 16.** Reverse Recovery Energy vs. External Gate Resistance

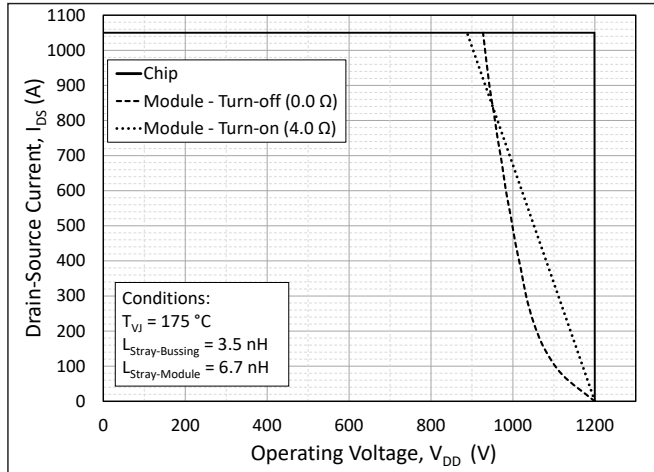


**Figure 17.** MOSFET Junction to Fluid Transient Thermal Impedance,  $Z_{th,JF}$  ( $^\circ\text{C/W}$ )

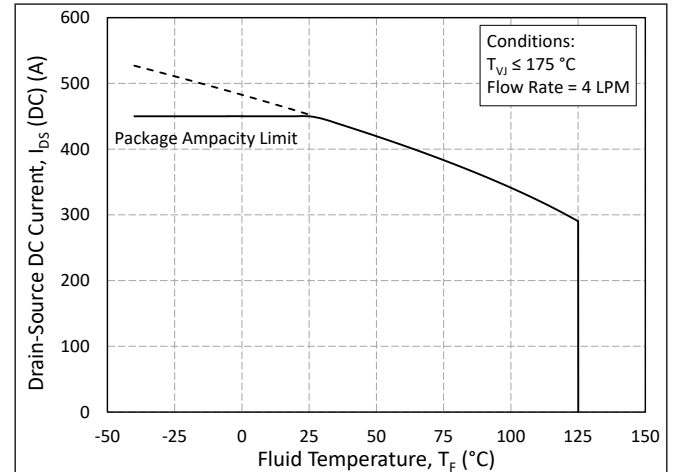


**Figure 18.** Forward Bias Safe Operating Area (FBSOA)

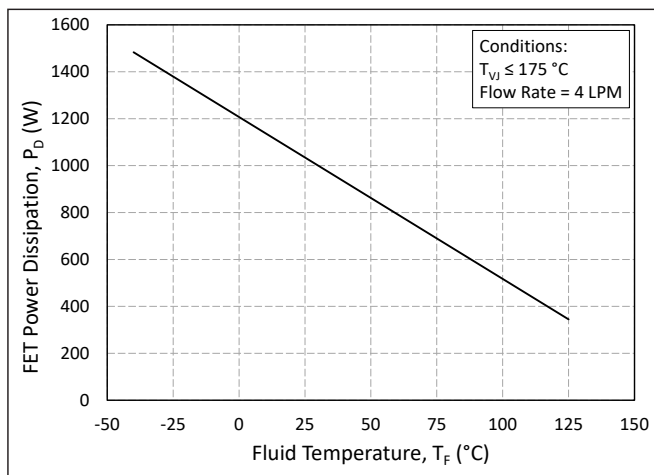
## Typical Performance



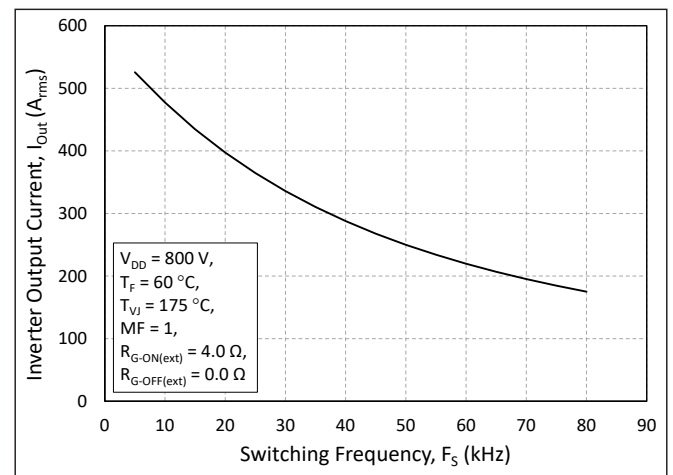
**Figure 19.** Switching Safe Operating Area



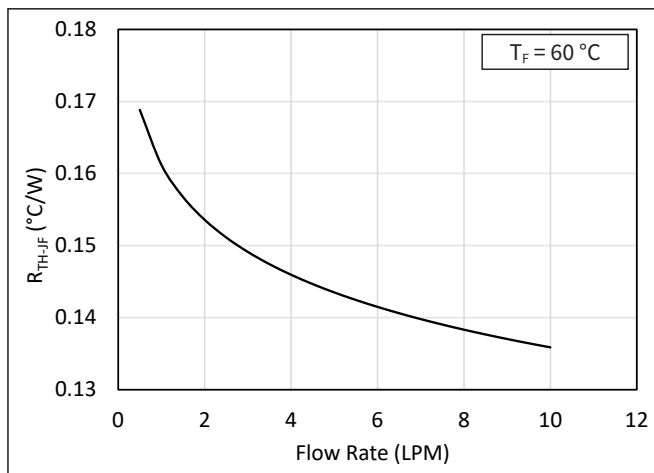
**Figure 20.** Continuous Drain Current Derating vs. Liquid Temperature



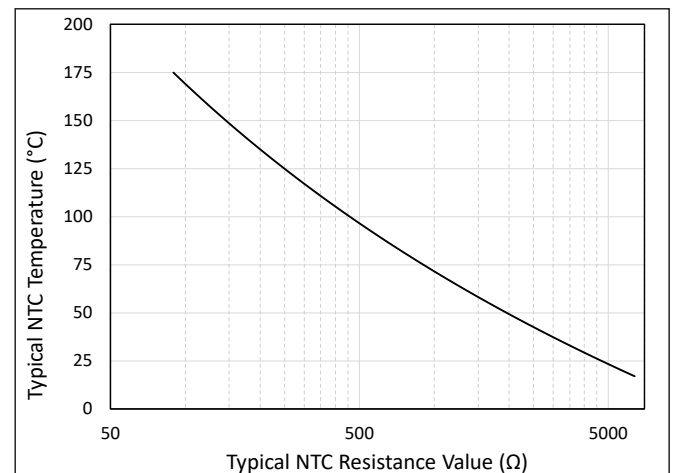
**Figure 21.** Maximum Power Dissipation Derating vs. Liquid Temperature



**Figure 22.** Typical Output Current Capability vs. Switching Frequency (Inverter Application)



**Figure 23.** Typical  $R_{TH-JF}$  vs Flow Rate



**Figure 24.** Typical NTC Resistance vs. Temperature

## Timing Characteristics

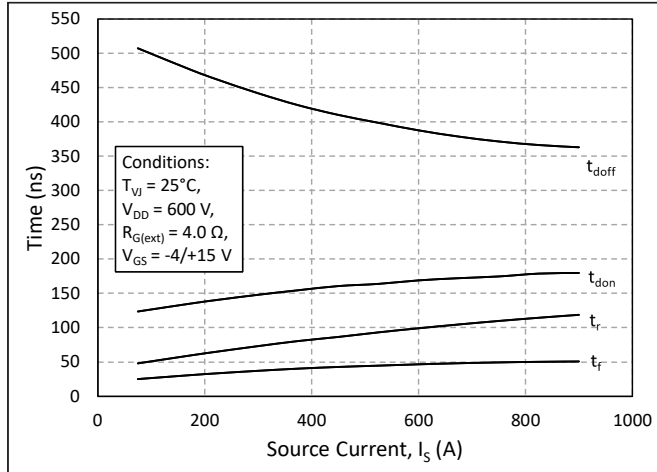


Figure 25. Timing vs. Source Current

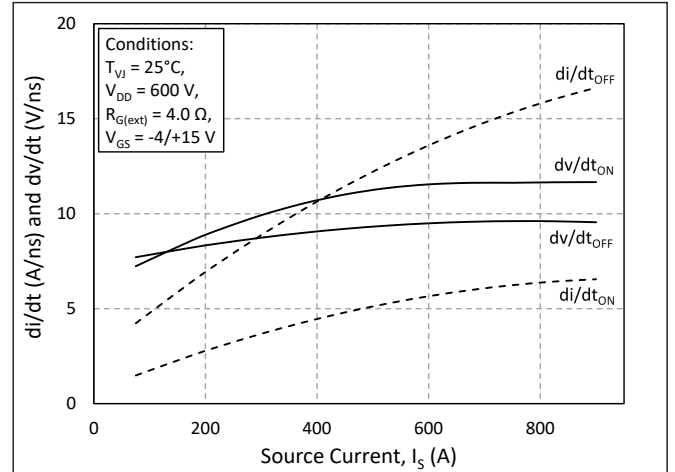
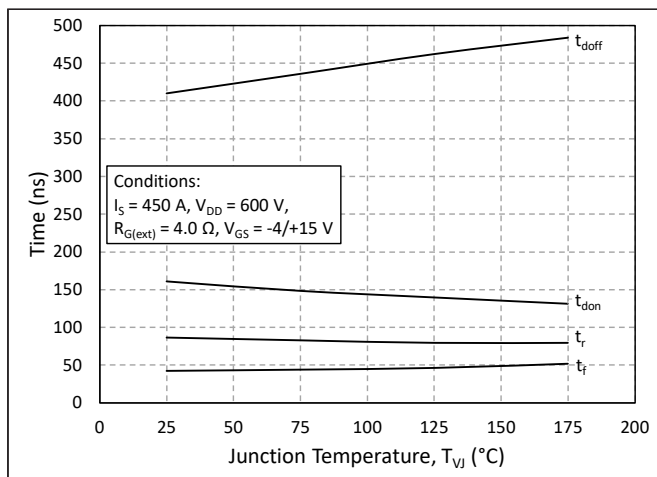
Figure 26.  $dv/dt$  and  $di/dt$  vs. Source Current

Figure 27. Timing vs. Junction Temperature

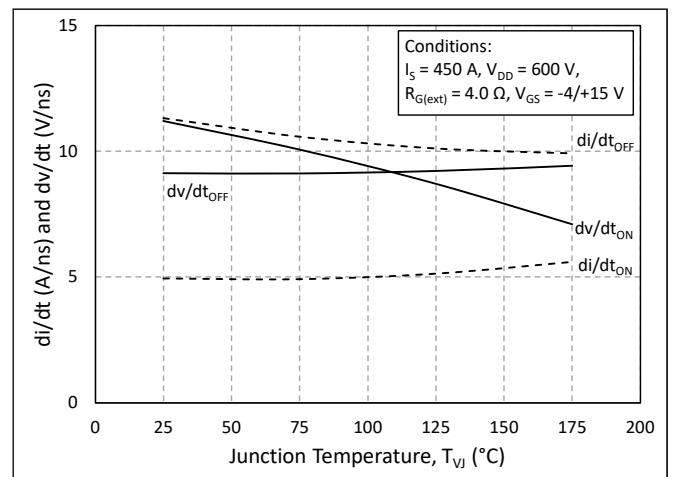
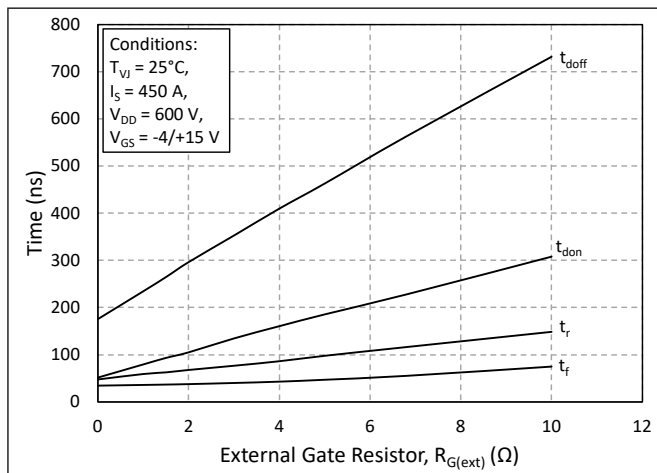
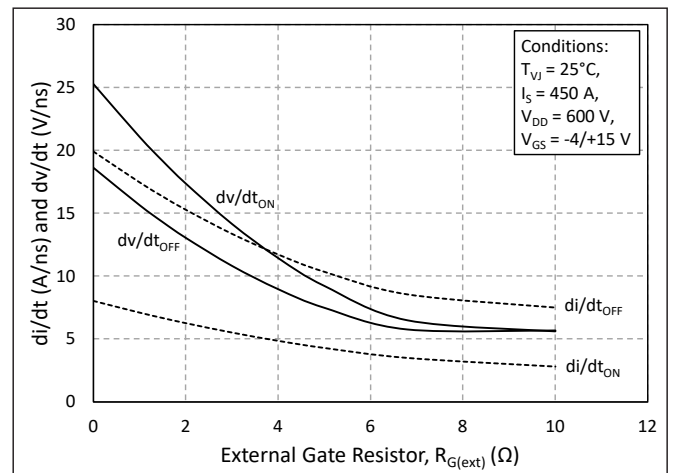
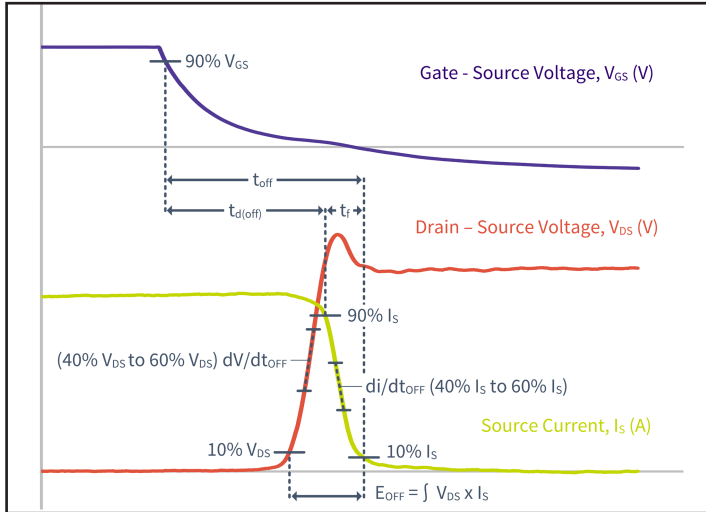
Figure 28.  $dv/dt$  and  $di/dt$  vs. Junction Temperature

Figure 29. Timing vs. External Gate Resistance

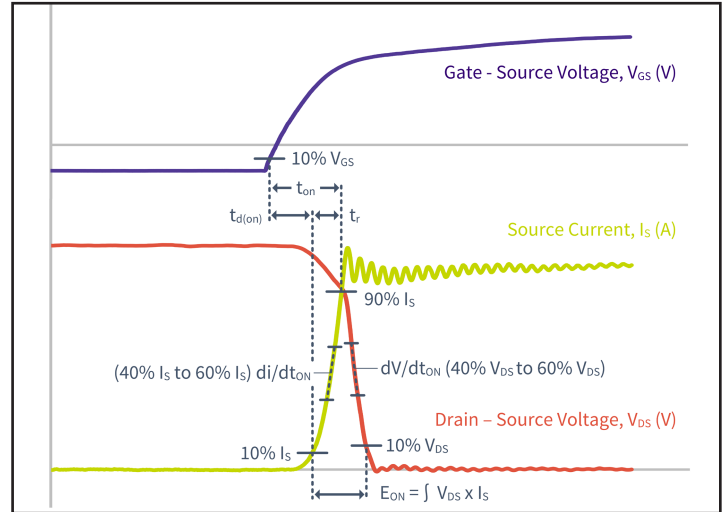
Figure 30.  $dv/dt$  and  $di/dt$  vs. External Gate Resistance



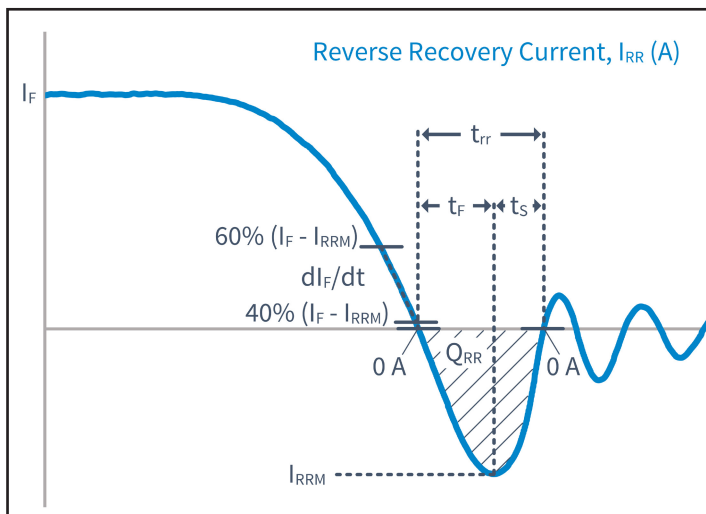
## Definitions



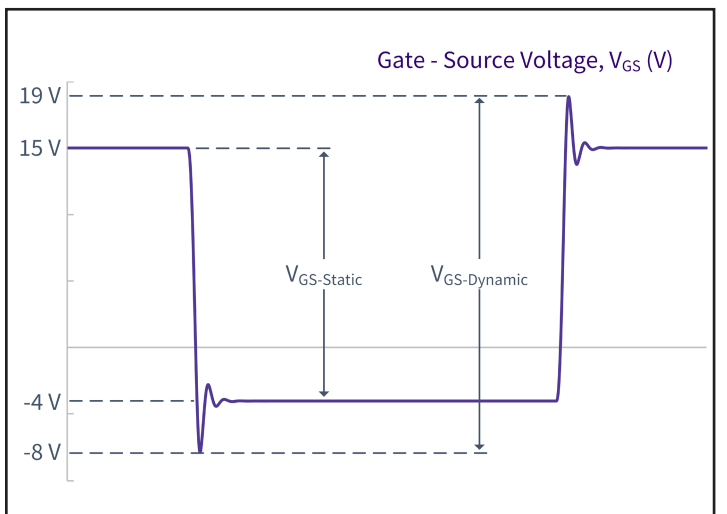
**Figure 31.** Turn-off Transient Definitions



**Figure 32.** Turn-on Transient Definitions

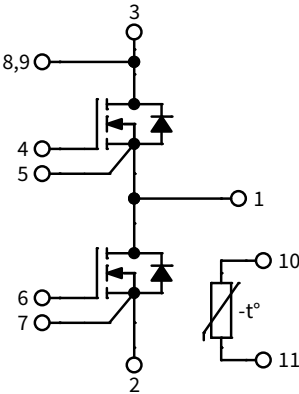
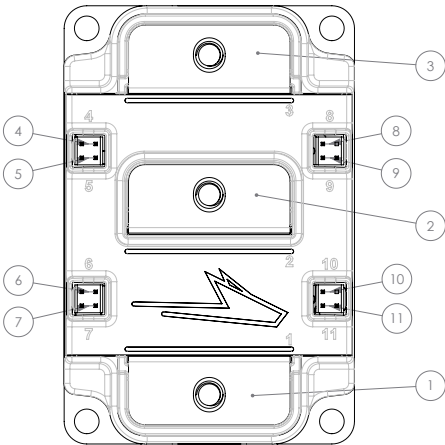


**Figure 33.** Reverse Recovery Definitions

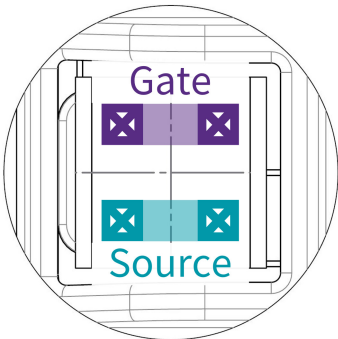


**Figure 34.**  $V_{GS}$  Transient Definitions

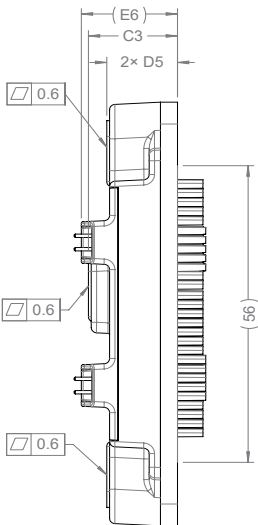
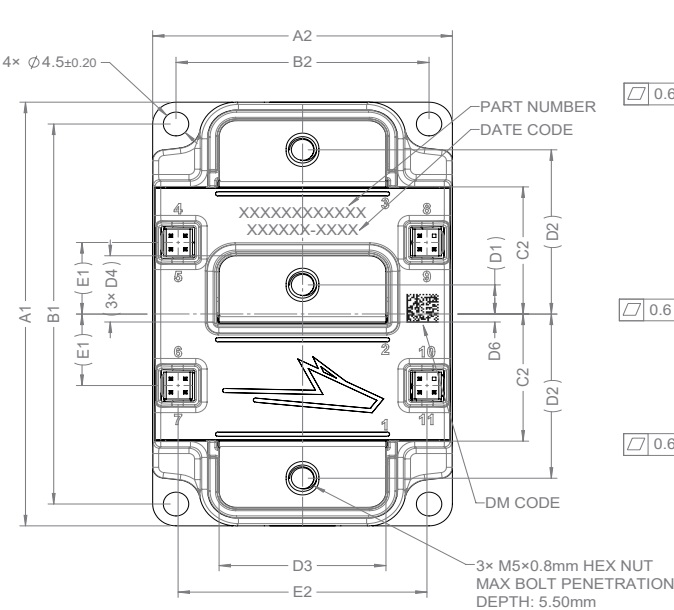
Schematic and Pin Out



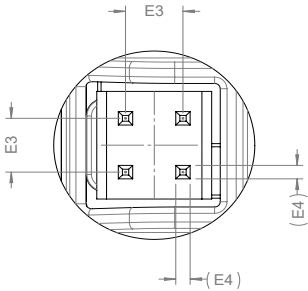
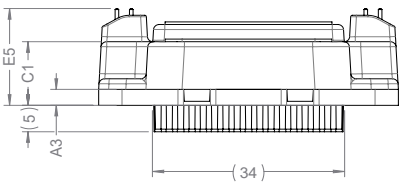
Zoom View of Signal Pinout



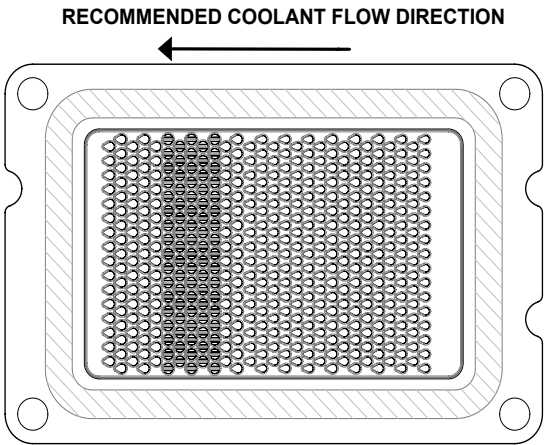
Package Dimension (mm)



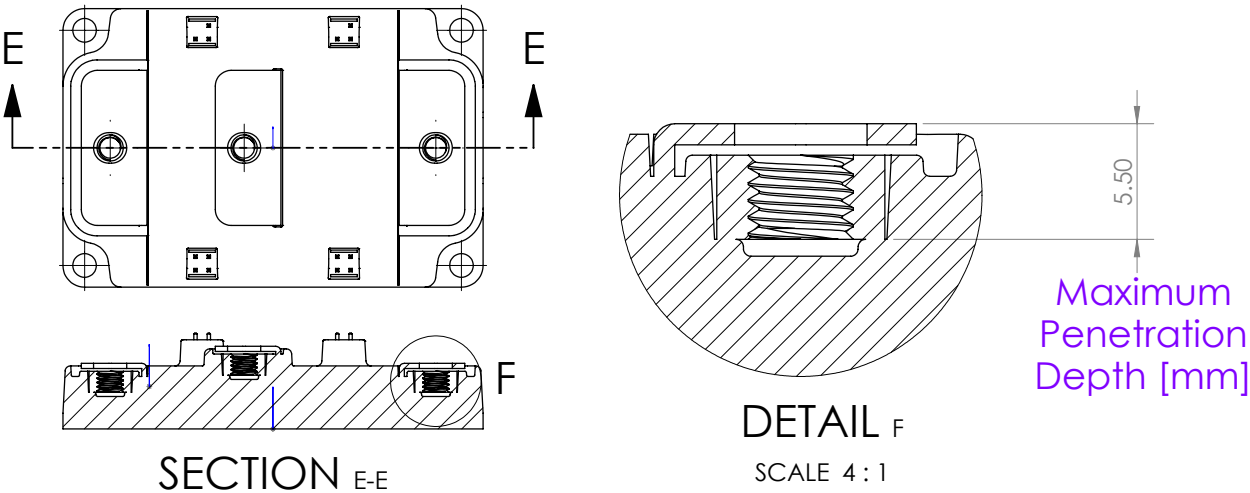
DIMENSION TABLE		
SYMBOL	DIMENSION	TOLERANCE
A1	80.00	±0.30
A2	53.00	±0.30
A3	3.00	±0.30
B1	71.75	±0.50
B2	44.75	±0.50
C1	12.00	+0.80 -0.30
C2	24.00	±0.90
C3	15.75	+1.52 -0.70
D1	(5.50)	REF.
D2	(31.00)	REF.
D3	29.50	±0.35
D4	(3x 12.50)	REF.
D5	2x 12.50	+1.51 -0.94
D6	1.50	±1.5
E1	(13.50)	REF.
E2	44.00	±0.50
E3	2.54	±0.50
E4	(0.64)	REF.
E5	18.31	+1.07 -1.06
E6	(17.00)	REF.



PinFin Flow Direction



Package Dimensions (mm)





## Supporting Links & Tools

### Evaluation Tools & Support

- [All SiC Module PLECS Models](#)
- [All SiC Module LTspice Models](#)
- [KIT-CRD-CIL12N-XM3: Dynamic Performance Evaluation Board for the XM3 Module](#)
- [SpeedFit 2.0 Design Simulator™](#)
- [Technical Support Forum](#)

### Dual-Channel Gate Driver Board

- [CGD12HBXMP: XM3 Evaluation Gate Driver](#)
- [CGD12HB00D: Differential Transceiver Daughter Board Companion Tool for Differential Gate Drivers](#)
- [FRDMGD3160XM3EVM: GD3160 XM3 Half-Bridge Evaluation Kit](#)
- [UCC5880QEVM-057 Evaluating Gate Driver for Wolfspeed XM3 Modules](#)
- [UCC5880INVERTEREVM Evaluating Board for Wolfspeed XM3 Modules](#)
- [Si828x Gate Driver Boards for Wolfspeed XM3 Modules](#)

### Application Notes

- [XM Module Signal Pinout Clarification Guide](#)
- [XM Mounting Guide](#)
- [XM3 Thermal Interference Material Guide](#)
- [Thermal Characterization Methods and Applications](#)
- [PRD-06832: Design Options for Wolfspeed® Silicon Carbide MOSFET Gate Bias Power Supplies](#)



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### **Contact info:**

4600 Silicon Drive  
Durham, NC 27703 USA  
Tel: +1.919.313.5300  
[www.wolfsp speed.com/power](http://www.wolfsp speed.com/power)